6020K/H

60V N -Channel MOSFET

- **N-Channel:60V 20A**
- **RDS(on)Typ= 23mΩ@VGS = 10 V**
- **RDS(on)Typ= 28mΩ@VGS =4.5 V**

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General Description

This Power MOSFET is produced using Maple semi's advanced TRENCH technology.

This advanced technology has been especially tailored to minimize conduction loss, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode.

Application

- PWM Application
- Load Switch
- Power Management

Package



Marking and pin assignment

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Absolute Maximum Ratings (T_C=25℃unless otherwise specified)

Symbol	Parameter	SLD20N06T	Units
V_{DSS}	Drain-Source Voltage	60	V
ID	Drain Current - Continuous (TC= 25℃)	20	A
	- Continuous (TC= 100℃)	14	A
IDM	Drain Current - Pulsed (Note 1)	60	A
VGSS	Gate-Source Voltage	±20	V
EAS	Single Pulsed Avalanche Energy	72	mJ
PD	Power Dissipation (TC = 25℃)	45	W
$R_{\theta JC}$	Thermal Resistance, Junction to Case	2.72	℃/W
TJ TSTG	Operating and Storage Temperature Range	-55 to +150	℃
TL	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	℃

* Drain current limited by maximum junction temperature.

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